

Abstracts

High performance circuits in 0.18 μm SiGe BiCMOS process for wireless applications (2002 [RFIC])

Peihua Ye, B. Agarwal, M. Reddy, L. Li, J. Cheng, P.C. Mudge, E. McCarthy and S.L. Lloyd. "High performance circuits in 0.18 μm SiGe BiCMOS process for wireless applications (2002 [RFIC])." 2002 Radio Frequency Integrated Circuits (RFIC) Symposium 02. (2002 [RFIC]): 329-332.

Silicon germanium bipolar CMOS (SiGe BiCMOS) process technology is gaining increasing popularity for RF circuits in wireless applications due to high performance, low cost, high yield and higher levels of integration with mixed signal and digital CMOS circuits. Four test circuits were designed and fabricated in Conexant's 0.18 μm SiGe BiCMOS process to evaluate the performance benefits provided by this state of the art process technology. The RF performance achieved in this process clearly makes this a process of choice for future RFIC products.

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